



TO-126 (SOT-32) Plastic Package

CSB631, CSB631K CSD600, CSD600K

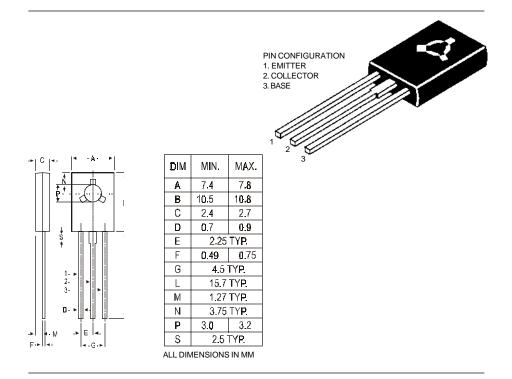
631

max. 100

631K

120 V

CSB631, 631KPNP PLASTIC POWER TRANSISTORSCSD600, 600KNPN PLASTIC POWER TRANSISTORSLow frequency Power Amplifier and Medium Speed Switching Applications



ABSOLUTE MAXIMUM RATINGS

Collector-emitter voltage (open base)

			600 600K)K
Collector-base voltage (open emitter)	V_{CBO}	max.	100	120	V
Collector-emitter voltage (open base)	V_{CEO}	max.	100	120	V
Collector current	I_C	max.	1.	0	Α
Total power dissipation up to $T_C = 25^{\circ}C$	P_C	max.	8.0		W
Junction temperature	T_i	max.	15	50	$^{\circ}\!C$
Collector-emitter saturation voltage	5				
$I_C = 0.5 \ A; \ I_B = 50 \ mA$	V _{CEsat}	max.	0.4		V
D.C. current gain					
$I_C = 50 \text{ mA}; V_{CE} = 5 V$	h _{FE}	min.	60		
		max.	32	20	
RATINGS (at $T_A=25^{\circ}C$ unless otherwise specified)				
Limiting values					
Collector-base voltage (open emitter)	V_{CBO}	max.	100	120	V

 V_{CEO}

CSB631, CSB631K CSD600, CSD600K

631

631K

			(600	60	0K
Emitter-base voltage (open collector)		V_{EBO}	max.	5	.0	V
Collector current		I_C	max.	1	.0	A
Collector current (peak)		I _{CP}	max.	2	.0	mA
Total power dissipation up to $T_A =$	25°C	P_C	max.	1	.0	W
Total power dissipation up to T_C =	25°C	P_C	max.	8	.0	W
Junction temperature		T_j	max.	15	50	⁰С
Storage temperature		\check{T}_{stg}	-65 to +150 °C		⁰С	
CHARACTERISTICS						
$T_{amb} = 25^{\circ}C$ unless otherwise specified	fied					
			631 631K 600 600K			
Collector cutoff current			•		20	
$I_E = 0; V_{CB} = 50 V$		I _{CBO}	max.	1	.0	μA
Emitter cut-off current						
$I_{C} = 0; V_{EB} = 4 V$		I _{EBO}	max.	1	.0	μA
Breakdown voltages						
$I_C = 1 mA; I_B = 0$		V_{CEO}	min.	100	120	V
$I_C = 10 \ \mu A; \ I_E = 0$		V_{CBO}	min.	100	120	V
$I_E = 10 \ \mu A; \ I_C = 0$		V_{EBO}	min.	5	.0	V
Saturation voltages						
$I_C = 500 \text{ mA}; I_B = 50 \text{ mA}$		V _{CEsat}	max.	0	.4	V
		V _{BEsat}	max.	1	.2	V
D.C. current gain						
$I_C = 50 \text{ mA}; V_{CE} = 5 V$		h_{FE}^*	min.	6	80	
			max.	32	20	
$I_C = 500 \text{ mA}; V_{CE} = 5 \text{ V}$		h _{FE}	min.	2	20	
Transition frequency						
$I_C = 50 \text{ mA}; V_{CE} = 10 \text{ V}$	PNP	f_T	typ.	11	0	MHz
-	NPN		typ.	13	80	MHz
Output capacitance						
$V_{CB} = 10 V; I_E = 0; f = 1 MHz$	PNP	Cob	typ.	3	80	pF
	NPN	Cab	typ.	2	20	pF

* h_{FE} classification: D60 - 120, E = 100 - 200, F 160 - 320

Customer Notes

Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Discrete Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished on the CDIL Web Site/CD are believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Discrete Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

CDIL strives for continuous improvement and reserves the right to change the specifications of its products without prior notice.



CDIL is a registered Trademark of Continental Device India Limited C-120 Naraina Industrial Area, New Delhi 110 028, India. Telephone + 91-11-2579 6150, 5141 1112 Fax + 91-11-2579 5290, 5141 1119 email@cdil.com www.cdilsemi.com

Data Sheet